ELECTRONICS, INC.
44 FARRAND STREET
BLOOMFIELD, NJ 07003
(973) 748–5089

NTE1317
Integrated Circuit
Module, 2 Power, 2 Channel, AF Power Amplifier, 50W Min.

Features:
- Muting Circuit
- Reduced Heat Sink due to Case Temperature Dissipation up to +125°C

Absolute Maximum Ratings: (T_A = +25°C unless otherwise specified)

Supply Voltage, V_{CC}max . . . . . ±53.0V
Operating Junction Temperature, T_J . . . . . +150°C
Substrate Temperature, T_C . . . . . +125°C
Storage Temperature Range, T_{stg} . . . . . –30° to +125°C
Thermal Resistance, Junction–to–Case, R_{thJC} . . . . . 1.8°C/W
Turn–on Time (V_{CC} = ±35V, R_L = 8Ω, f = 50Hz, P_O = 50W), t_s 2sec

Recommended Operating Conditions: (T_A = +25°C unless otherwise specified)

Supply Voltage, V_{CC} . . . . . ±35V
Load Resistance, R_L 8Ω

Electrical Characteristics: (T_A = 25°C, V_{CC} = ±35V, R_L = 8Ω, R_g = 600Ω, V_G = 40dB unless otherwise specified)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Idle Current	I_{CCO}	V_{CC} = ± 42.5V	20	40	100	mA
Power Out	P_O	THD = 0.8%,f = 20Hz to 20kHz	50	–	–	W
		V_{CC} = ±32V, THD = 0.2%, R_L = 4Ω, f = 1kHz	55	–	–	W
Total Harmonic Distortion	THD	P_O = 1.0W, f = 1kHz	–	–	0.08	%
Breakpoints	f_L, f_H	P_O = 1.0W, +0 –3dB	20 to 50k			Hz
Source Impedance	ri	P_O = 1.0W, f = 1kHz	–	55	–	kΩ
Input Noise Voltage	V_{NO}	V_{CC} = ±42.5V, R_g = 10kΩ	–	–	1.2	mV_{rms}
Transient Noise Voltage	V_N	V_{CC} = ±42.5V	–70	0	70	mV
Muting Voltage	V_M		–2	–5	–10	V

Pin Connection Diagram
(Front View)